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# NTHD3133PF

## Power MOSFET and Schottky Diode

-20 V, FETKY™, P-Channel, -4.4 A, with 3.7 A Schottky Barrier Diode, ChipFET™

### Features

- Leadless SMD Package Featuring a MOSFET and Schottky Diode
- 40% Smaller than TSOP-6 Package
- Leadless SMD Package Provides Great Thermal Characteristics
- Independent Pinout to each Device to Ease Circuit Design
- Trench P-Channel for Low On Resistance
- Ultra Low V<sub>F</sub> Schottky
- These are Pb-Free Devices

### Applications

- Li-Ion Battery Charging
- High Side DC-DC Conversion Circuits
- High Side Drive for Small Brushless DC Motors
- Power Management in Portable, Battery Powered Products

### MOSFET MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Units	
Drain-to-Source Voltage	V <sub>DSS</sub>	-20	V	
Gate-to-Source Voltage	V <sub>GS</sub>	±8.0	V	
Continuous Drain Current (Note 1)	Steady State	T <sub>J</sub> = 25°C	I <sub>D</sub> -3.2	A
		T <sub>J</sub> = 85°C	-2.3	
		t ≤ 5 s	T <sub>J</sub> = 25°C	-4.4
Power Dissipation (Note 1)	Steady State	T <sub>J</sub> = 25°C	P <sub>D</sub> 1.1	W
		t ≤ 5 s	2.1	
Pulsed Drain Current	t <sub>p</sub> = 10 μs	I <sub>DM</sub> -13	A	
Operating Junction and Storage Temperature	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	
Source Current (Body Diode)	I <sub>S</sub>	2.5	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T <sub>L</sub>	260	°C	

### SCHOTTKY DIODE MAXIMUM RATINGS

(T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Units	
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	20	V	
DC Blocking Voltage	V <sub>R</sub>	20	V	
Average Rectified Forward Current	Steady State	T <sub>J</sub> = 25°C	I <sub>F</sub> 2.2	V
		t ≤ 5 s	3.7	A

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



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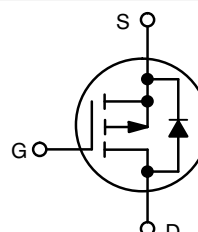
http://onsemi.com

### MOSFET

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> TYP	I <sub>D</sub> MAX
-20 V	64 mΩ @ -4.5 V	-4.4 A
	85 mΩ @ -2.5 V	

### SCHOTTKY DIODE

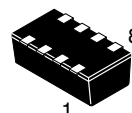
V <sub>R</sub> MAX	V <sub>F</sub> TYP	I <sub>F</sub> MAX
20 V	0.35 V	3.7 A



P-Channel MOSFET

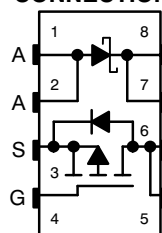


Schottky Diode

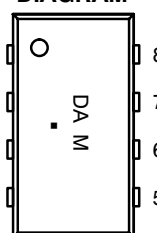


ChipFET  
CASE 1206A  
STYLE 3

### PIN CONNECTIONS



### MARKING DIAGRAM



DA = Specific Device Code  
 M = Month Code  
 ■ = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

## NTHD3133PF

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	113	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 10$ s (Note 2)	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$

2. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

### MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
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#### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-15		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$	$T_J = 25^{\circ}\text{C}$		-1.0	$\mu\text{A}$
			$T_J = 125^{\circ}\text{C}$		-5.0	
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			$\pm 100$	nA

#### ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.45		-1.5	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.7		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -3.2\text{ A}$		64	80	$\text{m}\Omega$
		$V_{GS} = -2.5\text{ V}, I_D = -2.2\text{ A}$		85	110	
		$V_{GS} = -1.8\text{ V}, I_D = -1.0\text{ A}$		120	170	
Forward Transconductance	$g_{FS}$	$V_{DS} = -10\text{ V}, I_D = -2.9\text{ A}$		8.0		S

#### CHARGES AND CAPACITANCES

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -10\text{ V}$		680		$\text{pF}$
Output Capacitance	$C_{OSS}$			100		
Reverse Transfer Capacitance	$C_{RSS}$			70		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}, I_D = -3.2\text{ A}$		7.4		$\text{nC}$
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	$Q_{GS}$			1.4		
Gate-to-Drain Charge	$Q_{GD}$			2.5		

#### SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -3.2\text{ A}, R_G = 2.4\ \Omega$		5.8		ns
Rise Time	$t_r$			11.7		
Turn-Off Delay Time	$t_{d(OFF)}$			16		
Fall Time	$t_f$			12.4		

#### DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = -2.5\text{ A}$	$T_J = 25^{\circ}\text{C}$		-0.8	-1.2	V
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}, di_S/dt = 100\text{ A}/\mu\text{s}$			13.5		ns
Charge Time	$t_a$				9.5		
Discharge Time	$t_b$				4.0		
Reverse Recovery Charge	$Q_{RR}$				6.5		

#### SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Maximum Instantaneous Forward Voltage	$V_F$	$I_F = 0.1\text{ A}$			0.31	V
		$I_F = 1.0\text{ A}$			0.365	
Maximum Instantaneous Reverse Current	$I_R$	$V_R = 10\text{ V}$			0.75	mA
		$V_R = 20\text{ V}$			2.5	
Non-Repetitive Peak Surge Current	$I_{FSM}$	Halfwave, Single Pulse 60 Hz			23	A

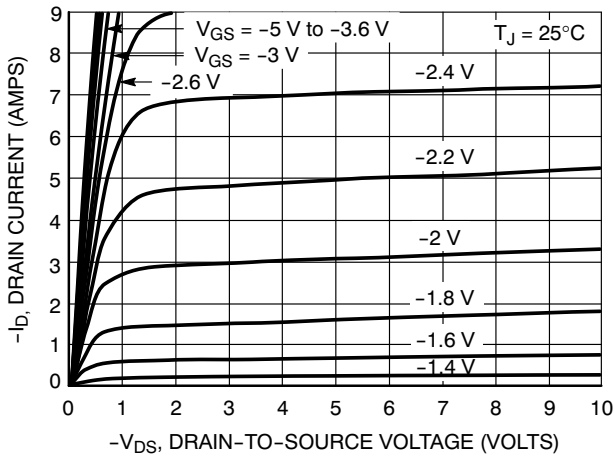
3. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

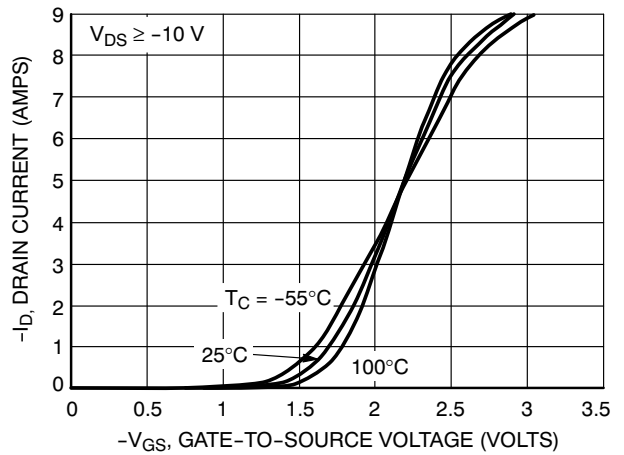
**NTHD3133PF**

**TYPICAL P-CHANNEL PERFORMANCE CURVES**

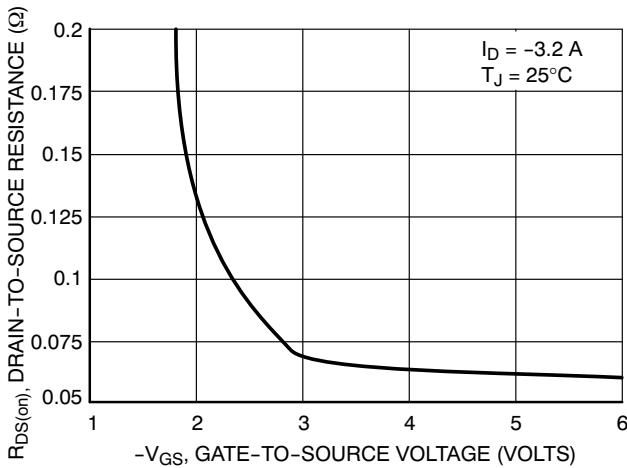
( $T_J = 25^\circ\text{C}$  unless otherwise noted)



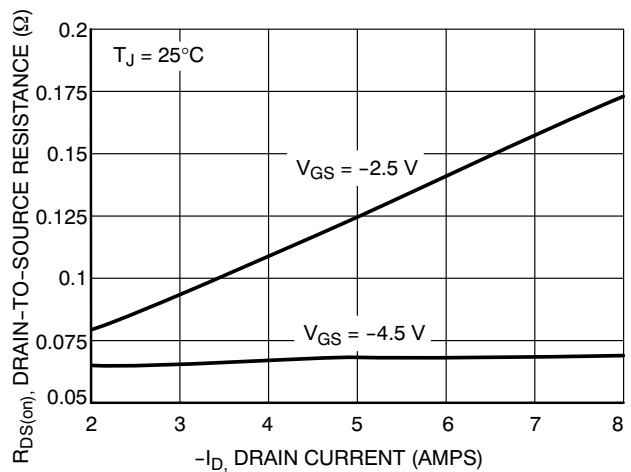
**Figure 1. On-Region Characteristics**



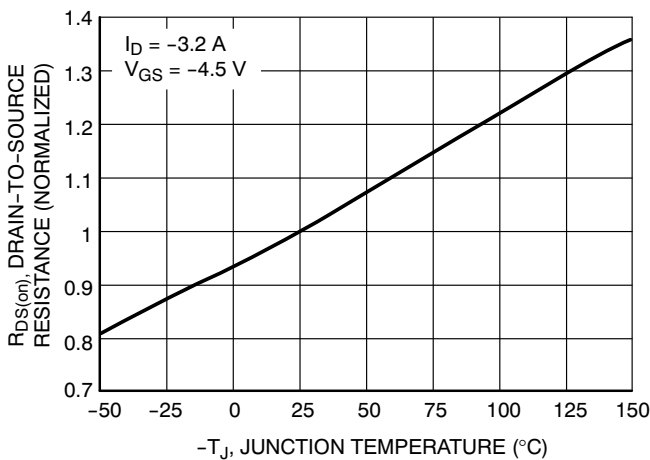
**Figure 2. Transfer Characteristics**



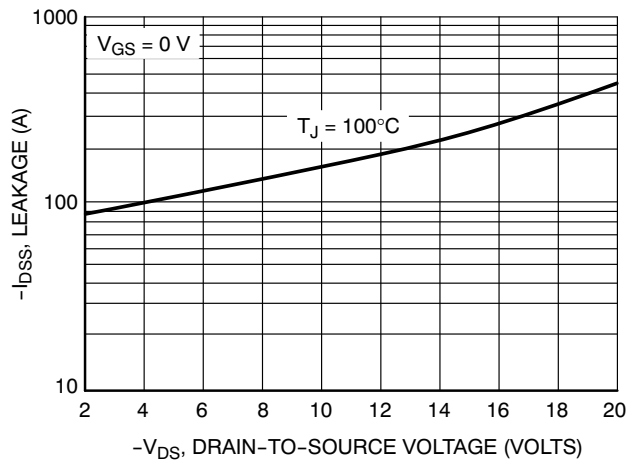
**Figure 3. On-Resistance vs. Gate-to-Source Voltage**



**Figure 4. On-Resistance vs. Drain Current and Gate Voltage**



**Figure 5. On-Resistance Variation with Temperature**

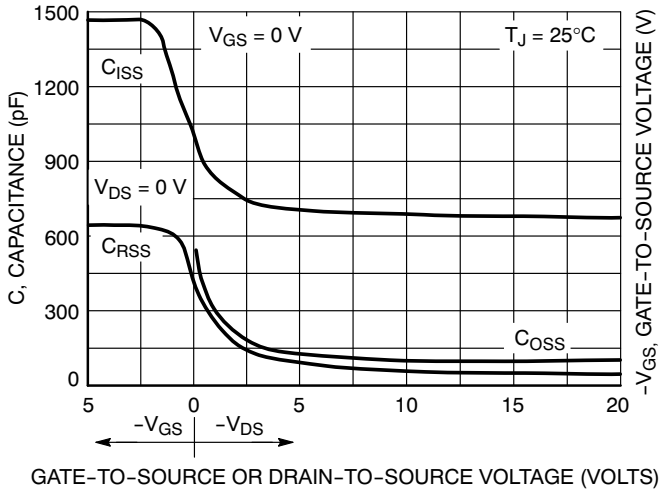


**Figure 6. Drain-to-Source Leakage Current vs. Voltage**

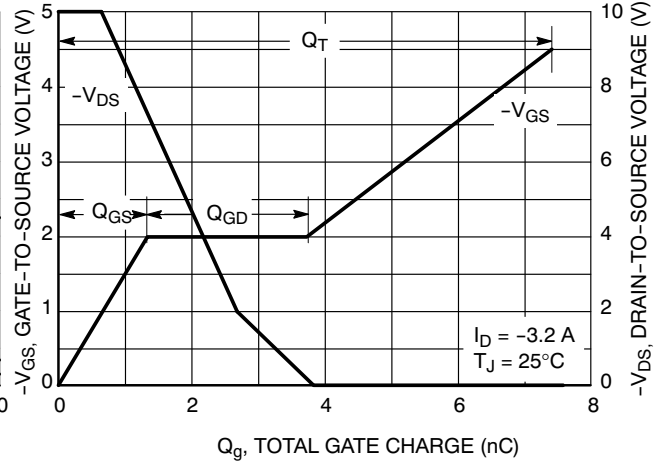
**NTHD3133PF**

**TYPICAL P-CHANNEL PERFORMANCE CURVES**

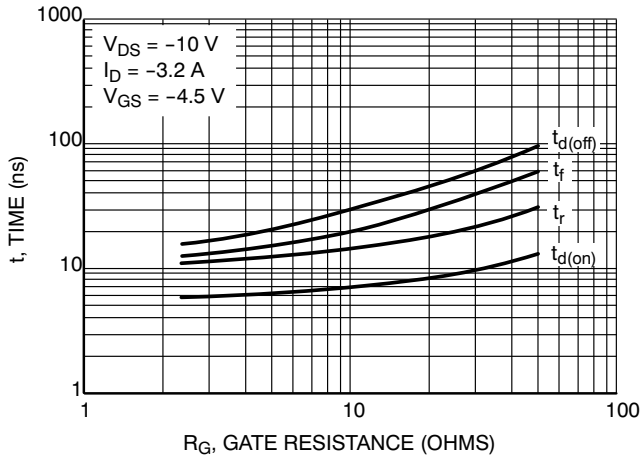
( $T_J = 25^\circ\text{C}$  unless otherwise noted)



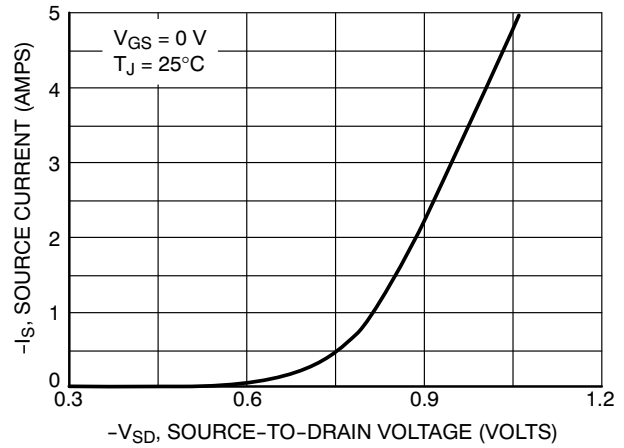
**Figure 7. Capacitance Variation**



**Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge**



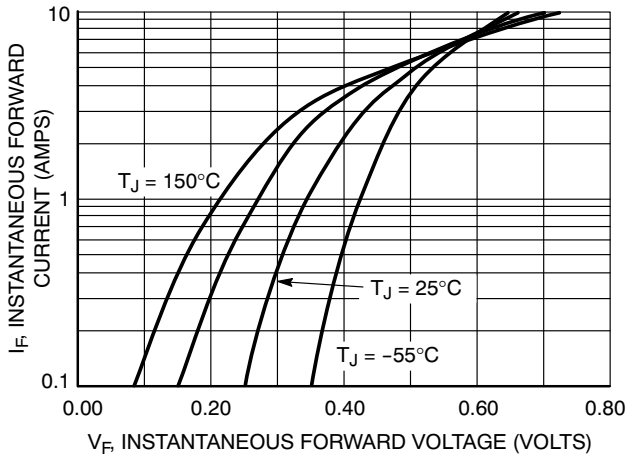
**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**



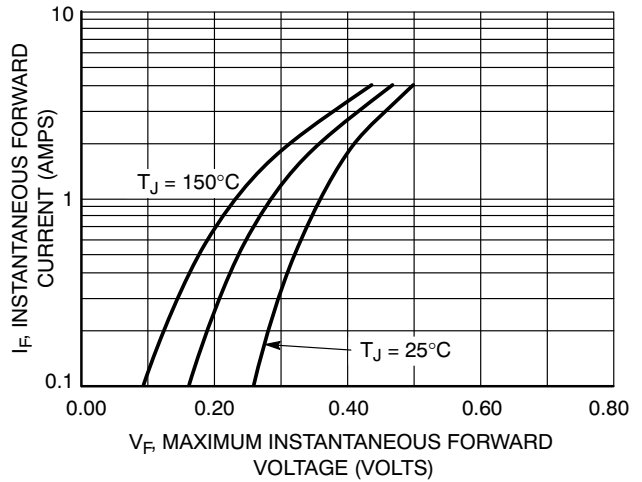
**Figure 10. Diode Forward Voltage vs. Current**

**NTHD3133PF**

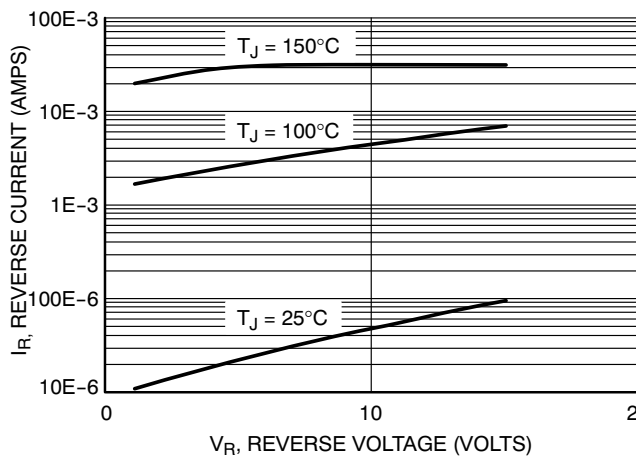
**TYPICAL SCHOTTKY PERFORMANCE CURVES** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)



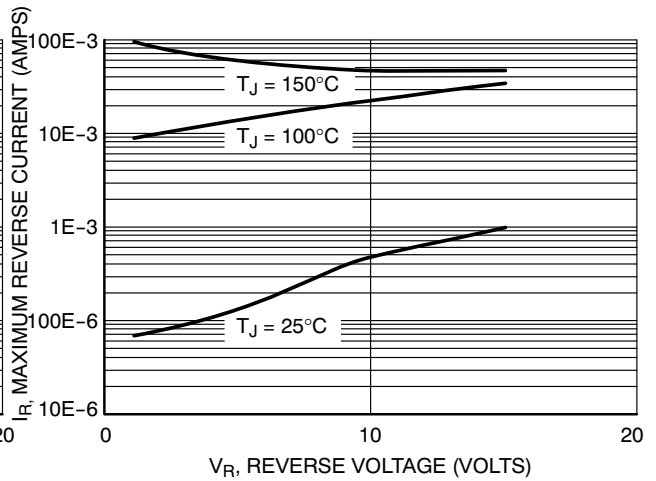
**Figure 11. Typical Forward Voltage**



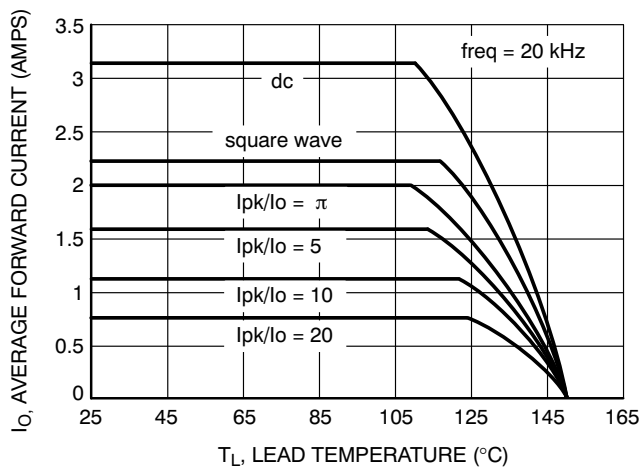
**Figure 12. Maximum Forward Voltage**



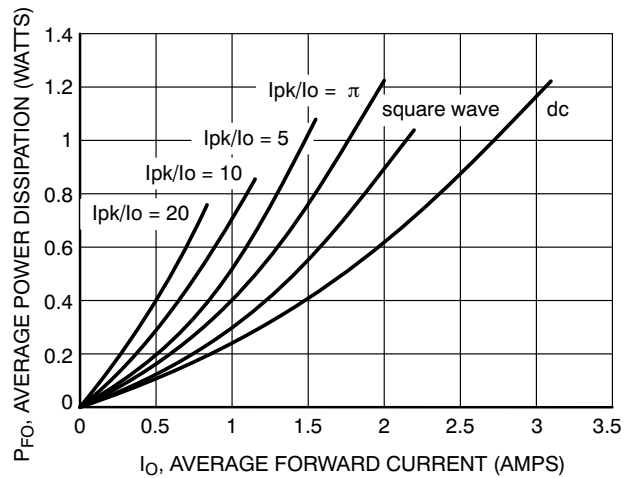
**Figure 13. Typical Reverse Current**



**Figure 14. Maximum Reverse Current**



**Figure 15. Current Derating**



**Figure 16. Forward Power Dissipation**

## NTHD3133PF

### DEVICE ORDERING INFORMATION

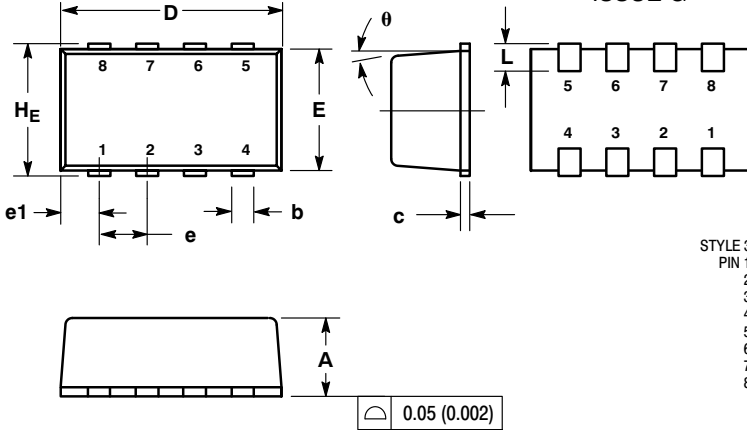
Device	Package	Shipping <sup>†</sup>
NTHD3133PFT1G	ChipFET (Pb-Free)	3000 / Tape & Reel
NTHD3133PFT3G	ChipFET (Pb-Free)	10000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## NTHD3133PF

### PACKAGE DIMENSIONS

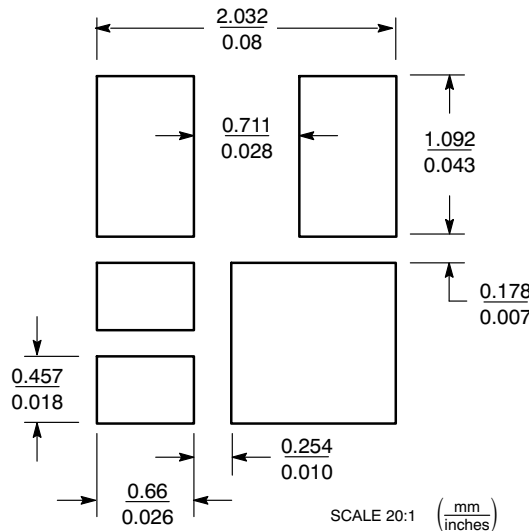
ChipFET  
 CASE 1206A-03  
 ISSUE G



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
  4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
  5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
  6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
HE	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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